

AMENDMENTS TO THE CLAIMS

This listing of claims will replace all prior versions, and listings, of claims in the application:

Listing of Claims:

1. (Previously Presented) A chamber structure of an inductive coupling plasma etching apparatus, comprising:
 - an etch chamber in which an etching process is performed;
 - a plasma chamber in which plasma is generated; and
 - a segregation wall part having a portion made of quartz opposite to the plasma chamber and having a portion made of a non-quartz ceramic opposite to the etch chamber, the segregation wall part separating the etch chamber from the plasma chamber.
2. (Original) The chamber structure of claim 1, wherein the plasma chamber is in an upper portion of the chamber structure, and the etch chamber is in a lower portion of the chamber structure.
3. (Original) The chamber structure of claim 1, which is of cylindrical shape.
4. (Previously Presented) The chamber structure of claim 1, wherein the portion of the segregation wall part opposite to the etch chamber includes a heater that heats the non-quartz ceramic portion.
5. (Original) The chamber structure of claim 1, wherein the segregation wall part includes gas flow paths and gas exhaust holes that supply process gas into the etch chamber.

6. (Previously Presented) A chamber structure of an inductive coupling plasma etching apparatus, the chamber structure having cylindrical shape and being divided by one segregation wall part into a first chamber wherein an etching process is performed and a second chamber in which plasma is generated,

the segregation wall part having a portion made of quartz that is a bottom of the second chamber, and having a portion made of non-quartz ceramic that is a ceiling of the first chamber.

7. (Original) The chamber structure of claim 6, wherein the portion of the segregation wall part that is a ceiling of the first chamber includes a heater.

8. (Original) The chamber structure of claim 6, wherein the segregation wall part includes gas flow paths and gas exhaust holes that supply process gas into the first chamber.

9. (Currently Amended) A chamber structure of an inductive coupling plasma etching apparatus of cylindrical shape ~~divided into an upper chamber and a lower chamber by one segregation wall part, the chamber structure comprising:~~
a lower chamber including an electrostatic chuck adapted to hold a wafer thereon;

an upper chamber, including a high frequency radiation element and a process gas supply line disposed therein for supplying a process gas to the lower etching chamber; and

a segregation wall separating the upper chamber from the lower chamber, the segregation wall part having a portion made of quartz that is a bottom wall of the upper chamber, and a portion made of non-quartz ceramic that is a ceiling wall of the lower chamber.

10. (Original) The chamber structure of claim 9, wherein plasma is generated in the upper chamber.

11. (Original) The chamber structure of claim 9, wherein an etching process is performed in the lower chamber.

12. (Original) The chamber structure of claim 9, wherein the portion of the segregation wall part that is a ceiling wall of the lower chamber includes a heater.

13. (Original) The chamber structure of claim 9, wherein the segregation wall part includes gas flow paths and gas exhaust holes that supply process gas into the lower chamber.

14. (New) The chamber structure of claim 1, further comprising a gas shower housing installed in the segregation wall between the portion made of quartz opposite to the plasma chamber and the portion made of a non-quartz ceramic opposite to the etch chamber.

15. (New) The chamber structure of claim 14, further comprising a heater installed in the segregation wall between the portion made of quartz opposite to the plasma chamber and the portion made of a non-quartz ceramic opposite to the etch chamber.

16. (New) The chamber structure of claim 6, further comprising a gas shower housing installed in the segregation wall between the portion made of quartz and the portion made of a non-quartz ceramic.

17. (New) The chamber structure of claim 16, further comprising a heater installed in the segregation wall between the portion made of quartz and the portion made of a non-quartz ceramic.

18. (New) The chamber structure of claim 9, further comprising a gas shower housing installed in the segregation wall between the portion made of quartz and the portion made of a non-quartz ceramic.

19. (New) The chamber structure of claim 19, further comprising a heater installed in the segregation wall between the portion made of quartz and the portion made of a non-quartz ceramic.